

Amendments to the Specification

Please amend the paragraph on page 4, lines 12-16 as follows:

- a first region of the conductivity of the ~~third~~ second type located in a near-surface substrate layer, divided into a first 3.1, second 3.2 and third 3.3 portions by the regions of silicon dioxide 4, which are equipped with the first 5, second 6 and third 7 ohmic contacts and form the first 8, second 9 and third 10 p-n junctions with the substrate;

Please amend the paragraph on page 7, lines 4-8 as follows:

- photogenerated carriers, generated above the first heavily-doped region 11 of the same conductivity type as the substrate, are accumulated at the readout region of the space charge of p-n junction 9. In this case, said barrier region 11 prevents interpenetration of photogenerated carriers between the channel 14 for diffusion of the secondary charge carriers [[14]] and the readout region of spatial charge of p-n junction 9;

Please split the paragraph on page 7, lines 9-20 into two paragraphs as follows:

- photogenerated carriers, generated below the first heavily-doped region 11 of the same conductivity type as the substrate and above the second heavily-doped region 12 of the same conductivity type as the substrate are accumulated at the readout region of space charge of p-n junction 8. In this case, said barrier region 12 prevents interpenetration of photogenerated carriers between the channels for diffusion of the secondary charge carriers 14 and 15;

- photogenerated carriers generated below the second heavily-doped region 12 of the same conductivity type as the substrate and above the third heavily-doped region 13 of the same conductivity type as the substrate are accumulated at the readout region of the space charge of p-n junction 10. In this case, said barrier region 13 prevents interpenetration of the carriers photogenerated below the barrier region 13, which correspond to the infrared band of the optical spectrum, into the channel for diffusion of the secondary charge carriers 15;